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(71) Applicant *(for all designated States except US)*: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **XIANG, Qi** [CN/US]; 1119 Thames Drive, San Jose, CA 95129 (US). **PAN, James, N.** [--/US]; 3 Mountain View Knolls Drive, Apt. D, Fishkill, NY 12524 (US). **GOO, Jung-Suk** [KR/US]; 100 Escondido Village, #D, Stanford, CA 94305 (US).

(74) Agent: **DRAKE, Paul, S.**; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

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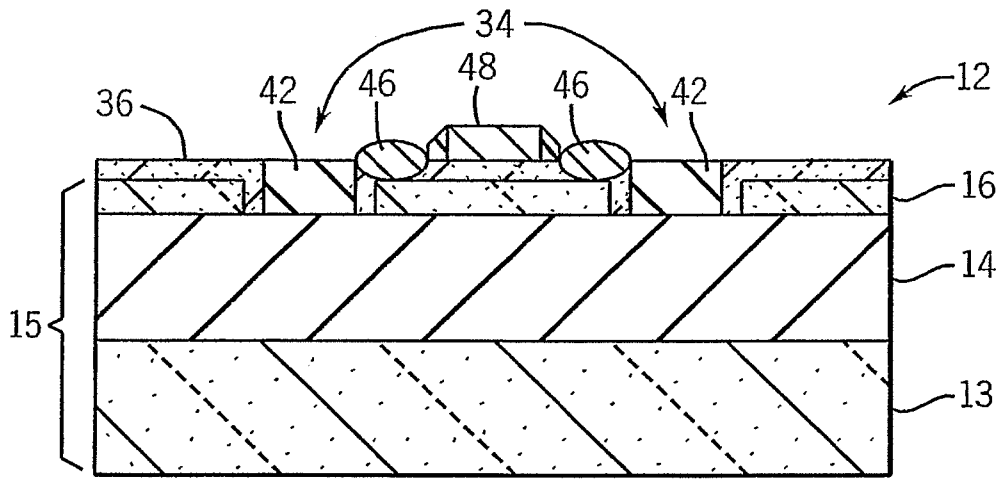
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(54) Title: SHALLOW TRENCH ISOLATION PROCESS AND STRUCTURE



(57) Abstract: A method of manufacturing an integrated circuit (IC) utilizes a shallow trench isolation (STI) technique. The shallow trench isolation technique is used in strained silicon (SMOS) process. The strained material (36) is formed after the trench (34) is formed. The process can be utilized on a compound semiconductor layer (15) above a buried oxide (Box) layer (14).

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